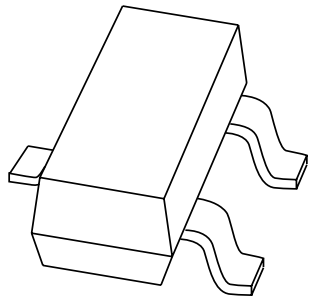


DATA SHEET



BCF32

NPN general purpose transistor

Product specification
Supersedes data of 1997 May 20

1999 Apr 22

NPN general purpose transistor

BCF32

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 32 V).

APPLICATIONS

- Low level, low noise general purpose applications in thick and thin-film circuits.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

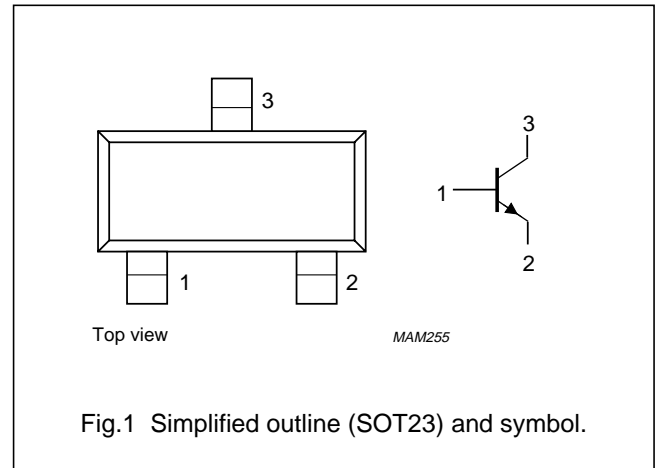
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCF32	D7*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	32	V
V _{CEO}	collector-emitter voltage	open base	–	32	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 32\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 32\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$	–	150	–	
		$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	200	–	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	210	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	750	–	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	850	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550	–	700	mV
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	1.2	4	dB

NPN general purpose transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

NPN general purpose transistor

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN general purpose transistor

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NOTES

NPN general purpose transistor

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NOTES

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